MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

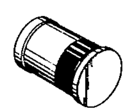
MLL746 thru MLL759
MLL957A thru MLL986A
MLL4370 thru MLL4372

500 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

- Complete Voltage Range — 2.4 to 110 Volts
- Leadless Package for Surface Mount Technology
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Nitride Passivated Die
- Available in 8 mm Tape and Reel
  T1 Cathode Facing Sprocket Holes
  T2 Anode Facing Sprocket Holes

LEADLESS GLASS ZENER DIODES

500 MILLIWATTS
2.4–110 VOLTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A \leq 50°C$ Derate above $T_A = 50°C$	P_D	500 3.3	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

MECHANICAL CHARACTERISTICS

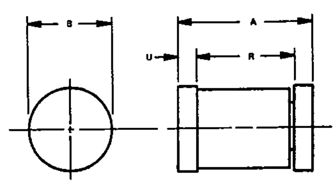
CASE: Double slug type, hermetically sealed glass

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, for 10 seconds

FINISH: All external surfaces are corrosion resistant and readily solderable

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode

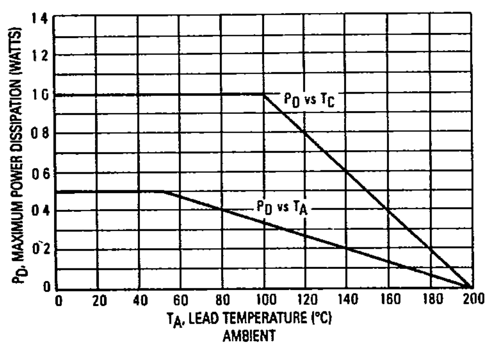
MOUNTING POSITION: Any



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

CASE 362-01 GLASS

STEADY STATE POWER DERATING



MLL746 thru MLL759, MLL957A thru MLL986A, MLL4370 thru MLL4372

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V Max @ 200 mA for all types)

Type Number (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} (Notes 1,2,3) Volts	Test Current I_{ZT} (Note 2) mA	Maximum Zener Impedance Z_{ZT} @ I_{ZT} (Note 4) Ohms	Maximum DC Zener Current I_{ZM} mA		Maximum Reverse Leakage Current T_A = 25°C I_R @ V_R = 1 V µA	Maximum Reverse Leakage Current T_A = 150°C I_R @ V_R = 1 V µA
MLL4370	2.4	20	30	150	190	100	200
MLL4371	2.7	20	30	135	165	75	150
MLL4372	3.0	20	29	120	150	50	100
MLL746	3.3	20	28	110	135	10	30
MLL747	3.6	20	24	100	125	10	30
MLL748	3.9	20	23	95	115	10	30
MLL749	4.3	20	22	85	105	2	30
MLL750	4.7	20	19	75	95	2	30
MLL751	5.1	20	17	70	85	1	20
MLL752	5.6	20	11	65	80	1	20
MLL753	6.2	20	7	60	70	0.1	20
MLL754	6.8	20	5	55	65	0.1	20
MLL755	7.5	20	6	50	60	0.1	20
MLL756	8.2	20	8	45	55	0.1	20
MLL757	9.1	20	10	40	50	0.1	20
MLL758	10	20	17	35	45	0.1	20
MLL759	12	20	30	30	35	0.1	20

Type Number (Note 1)	Nominal Zener Voltage V_Z (Notes 1,2,3) Volts	Test Current I_{ZT} (Note 2) mA	Maximum Zener Impedance (Note 4) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Maximum DC Zener Current I_{ZM} mA		Maximum Reverse Current I_R Maximum µA	Test Voltage Vdc V_R 5%	Test Voltage Vdc V_R 10%
MLL957A	6.8	18.5	4.5	700	1.0	47	61	150	5.2	4.9
MLL958A	7.5	16.5	5.5	700	0.5	42	55	75	5.7	5.4
MLL959A	8.2	15	6.5	700	05	38	50	50	6.2	5.9
MLL960A	9.1	14	7.5	700	0.5	35	45	25	6.9	6.6
MLL961A	10	12.5	8.5	700	0.25	32	41	10	7.6	7.2
MLL962A	11	11.5	9.5	700	0.25	28	37	5	8.4	8.0
MLL963A	12	10.5	11.5	700	0.25	26	34	5	9.1	8.6
MLL964A	13	9.5	13	700	0.25	24	32	5	9.9	9.4
MLL965A	15	8.5	16	700	0.25	21	27	5	11.4	10.8
MLL966A	16	7.8	17	700	0.25	19	37	5	12.2	11.5
MLL967A	18	7.0	21	750	0.25	17	23	5	13.7	13.0
MLL968A	20	6.2	25	750	0.25	15	20	5	15.2	14.4
MLL969A	22	5.6	29	750	0.25	14	18	5	16.7	15.8
MLL970A	24	5.2	33	750	0.25	13	17	5	18.2	17.3
MLL971A	27	4.6	41	750	0.25	11	15	5	20.6	19.4
MLL972A	30	4.2	49	1000	0.25	10	13	5	22.8	21.6
MLL973A	33	3.8	58	1000	0.25	9.2	12	5	25.1	23.8
MLL974A	36	3.4	70	1000	0.25	8.5	11	5	27.4	25.9
MLL975A	39	3.2	80	1000	0.25	7.8	10	5	29.7	28.1
MLL976A	43	3.0	93	1500	0.25	7.0	9.6	5	32.7	31.0
MLL977A	47	2.7	105	1500	0.25	6.4	8.8	5	35.8	33.8
MLL978A	51	2.5	125	1500	0.25	5.9	8.1	5	38.8	36.7
MLL979A	56	2.2	150	2000	0.25	5.4	7.4	5	42.6	40.3
MLL980A	62	2.0	185	2000	0.25	4.9	6.7	5	47.1	44.6
MLL981A	68	1.8	230	2000	0.25	4.5	6.1	5	51.7	49.0
MLL982A	75	1.7	270	2000	0.25	1.0	5.5	5	56.0	54.0
MLL983A	82	1.5	330	3000	0.25	3.7	5.0	5	62.2	59.0
MLL984A	91	1.4	400	3000	0.25	3.3	4.6	5	69.2	65.6
MLL985A	100	1.3	500	3000	0.25	3.0	4.5	5	76	72
MLL986A	110	1.1	750	4000	0.25	2.7	4.1	5	83.6	79.2

4

MLL746 thru MLL759, MLL957A thru MLL986A, MLL4370 thru MLL4372

NOTE 1. Tolerance Designation — The type numbers shown have tolerance designations as follows:

MLL4370 series: ±10%, suffix A for ±5% units.
MLL746 series: ±10%, suffix A for ±5% units.
MLL957 series: suffix A for ±10% units, suffix B for ±5% units.

NOTE 2. Special Selections† Available Include:

1. Nominal zener voltages between those shown.
2. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.
3. Nominal voltages at non-standard test currents.

NOTE 3. Zener Voltage (V_Z) Measurement — Nominal zener voltage is measured with the device junction in thermal equilibrium at the case temperature of 30°C ±1°C.

NOTE 4. Zener Impedance (Z_Z) Derivation — Z_{ZT} is measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac) = 0.1 \times I_Z(dc)$ with the ac frequency = 1.0 kHz.

†For more information on special selections contact your nearest Motorola representative.

4

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Case Temperature, T_C, should be determined from:

$$T_C = \theta_{CA}P_D + T_A.$$

θ_{CA} is the case-to-ambient thermal resisstance (°C/W) and P_D is the power dissipation. The value for θ_{CA} will vary and depends on the device mounting method. θ_{CA} is generally 200°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the case can also be measured using a thermocouple placed at the case end as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}.$$

ΔT_{JC} is the increase in junction temperature above the case temperature and may be found by using:

$$\Delta T_{JC} = \theta_{JC}P_D.$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ}\Delta T_J.$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

FIGURE 1 — TYPICAL LEAKAGE CURRENT

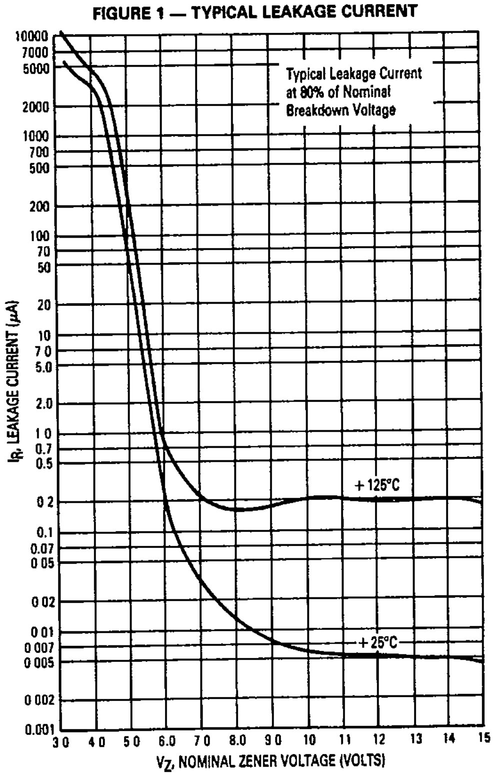


FIGURE 2 — TEMPERATURE COEFFICIENTS
(−55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

a — RANGE FOR UNITS TO 12 VOLTS / **b — RANGE FOR UNITS 12 TO 100 VOLTS**

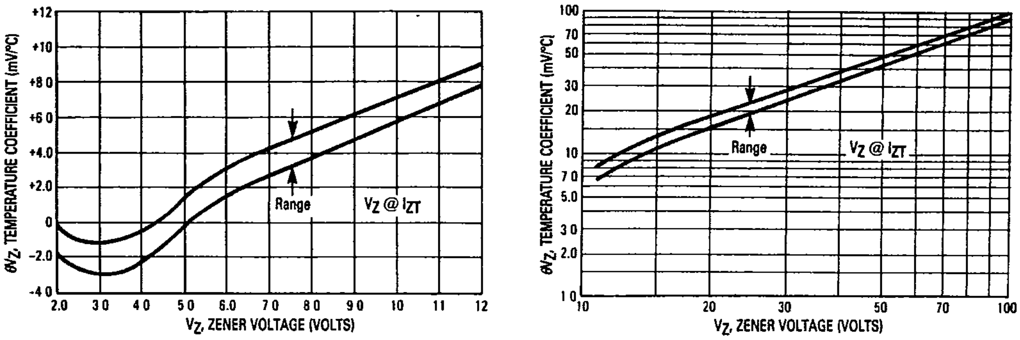


FIGURE 3 — EFFECT OF ZENER CURRENT

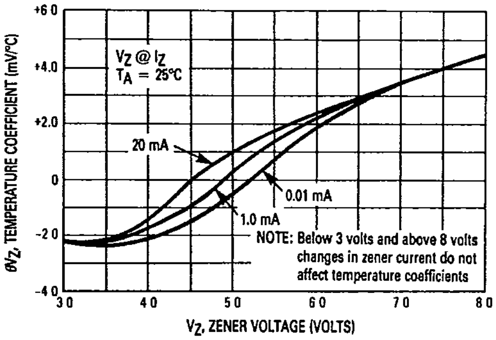


FIGURE 4 — TYPICAL CAPACITANCE

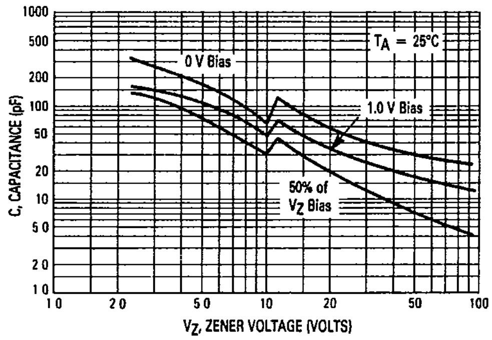
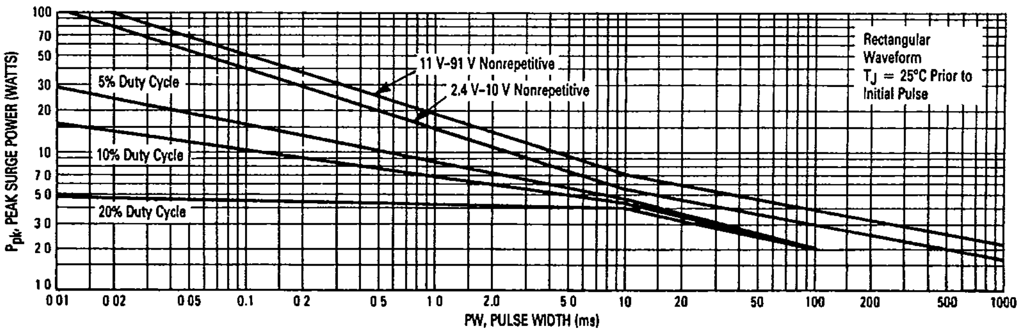


FIGURE 5 — MAXIMUM SURGE POWER



This graph represents 90 percentile data points.
For worst-case design characteristics, multiply surge power by 2/3.

MLL746 thru MLL759, MLL957A thru MLL986A, MLL4370 thru MLL4372

FIGURE 6 — EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

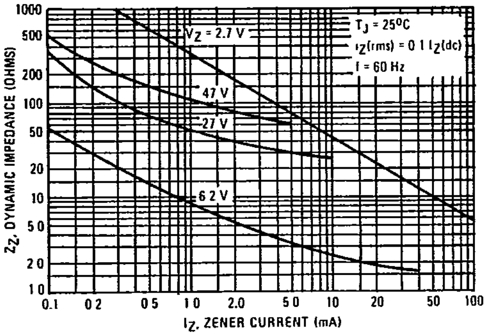


FIGURE 7 — EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

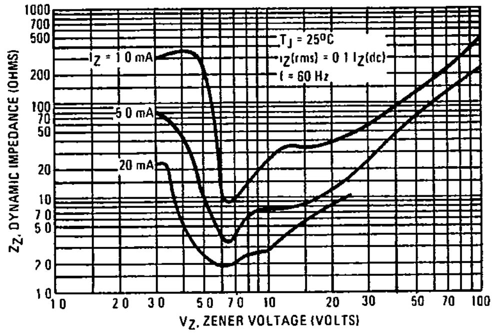


FIGURE 8 — TYPICAL NOISE DENSITY

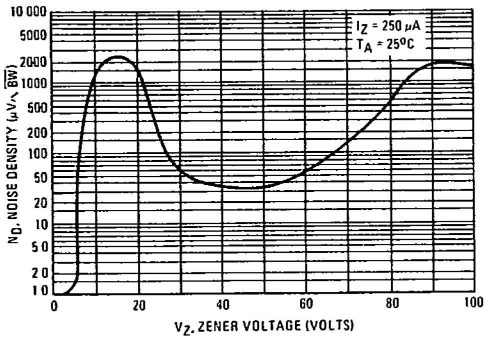
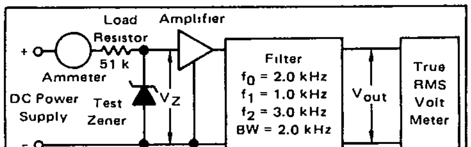


FIGURE 9 — NOISE DENSITY MEASUREMENT METHOD



$$\text{Noise Density (Volts Per Square Root Bandwidth)} = \frac{V_{out}}{\text{Overall Gain } \sqrt{BW}}$$

Where: BW = Filter Bandwidth (Hz)
V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

FIGURE 10 — TYPICAL FORWARD CHARACTERISTICS